



# STF16NK60Z STP16NK60Z, STW16NK60Z

N-channel 600 V, 038  $\Omega$ , 14 A, TO-220, TO-220FP, TO-247  
Zener-protected SuperMESH™ Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub>	P <sub>w</sub>
STF16NK60Z	600 V	< 0.42 $\Omega$	14 A <sup>(1)</sup>	40 W
STP16NK60Z	600 V	< 0.42 $\Omega$	14 A	190 W
STW16NK60Z	600 V	< 0.42 $\Omega$	14 A	190 W

1. Limited by package.

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

## Application

- Switching applications

## Description

The new SuperMESH™ series of Power MOSFETS is the result of further design improvements on ST's well-established strip-based PowerMESH™ layout. In addition to significantly lower on-resistance, the device offers superior dv/dt capability to ensure optimal performance even in the most demanding applications. The SuperMESH™ devices further complement an already broad range of innovative high voltage MOSFETS, which includes the revolutionary MDmesh™ products.

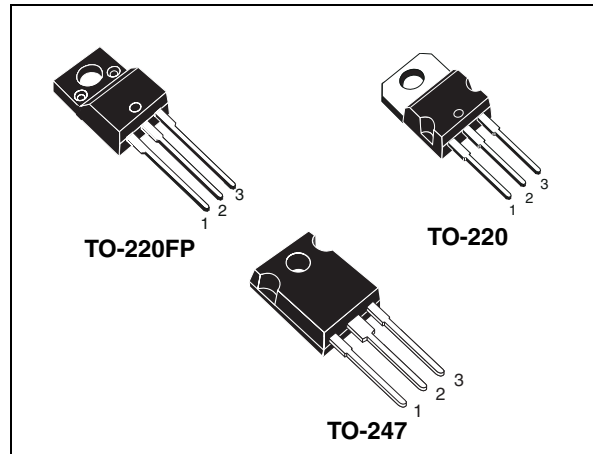


Figure 1. Internal schematic diagram

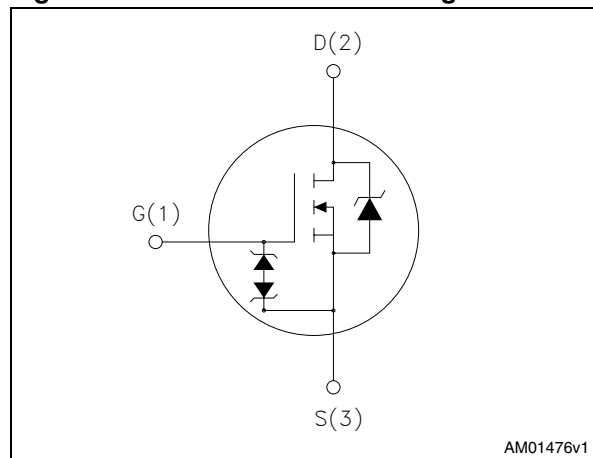


Table 1. Device summary

Order codes	Marking	Package	Packaging
STF16NK60Z	F16NK60Z	TO-220FP	Tube
STP16NK60Z	P16NK60Z	TO-220	
STW16NK60Z	W16NK60Z	TO-247	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220 / TO-247	TO-220FP	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	600		V
$V_{GS}$	Gate- source voltage	$\pm 30$		V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	14	14 <sup>(1)</sup>	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	8.8	8.8 <sup>(1)</sup>	A
$I_{DM}^{(2)}$	Drain current (pulsed)	56	56 <sup>(1)</sup>	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	190	40	W
	Derating factor	1.51		W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD(HBM-C = 100 pF, R = 1.5 k $\Omega$ )	6000		V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5		V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C = 25\text{ }^\circ\text{C}$ )		2500	V
$T_{stg}$	Storage temperature	-55 to 150		$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150		$^\circ\text{C}$

- Limited by package
- Pulse width limited by safe operating area
- $I_{SD} \leq 14\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$

**Table 3. Thermal data**

Symbol	Parameter	TO-220	TO-247	TO-220FP	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.66		3.1	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	50	62.5	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300			$^\circ\text{C}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Max value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	14	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	360	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	620			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_C = 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 7\text{ A}$		0.38	0.42	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	2650	-	pF
$C_{oss}$	Output capacitance			285		pF
$C_{rss}$	Reverse transfer capacitance			62		pF
$C_{OSS\text{ eq}}^{(1)}$	Equivalent output capacitance			158		pF
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 14\text{ A}$ ,	-	86	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10\text{ V}$		17		nC
$Q_{gd}$	Gate-drain charge	(see <a href="#">Figure 19</a> )		46		nC

1.  $C_{OSS\text{ eq}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{OSS}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 480\text{ V}$ , $I_D = 14\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 18</a> )	-	30	-	ns
$t_r$	Rise time			25		ns
$t_{d(off)}$	Turn-off-delay time			70		ns
$t_f$	Fall time			15		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		14	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		56	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 14\text{ A}, V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 14\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see <a href="#">Figure 23</a> )	-	490		ns
$Q_{rr}$	Reverse recovery charge			5.4		nC
$I_{RRM}$	Reverse recovery current			22		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 14\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}, T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 23</a> )	-	585		ns
$Q_{rr}$	Reverse recovery charge			7		nC
$I_{RRM}$	Reverse recovery current			24		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 9. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{gs} = \pm 1\text{ mA}$ (open drain)	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

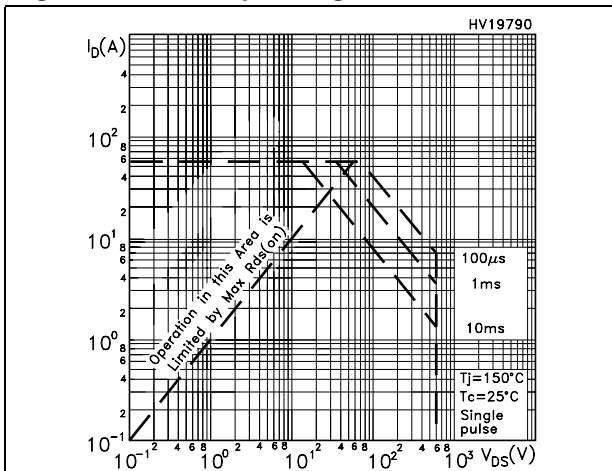


Figure 3. Thermal impedance for TO-220

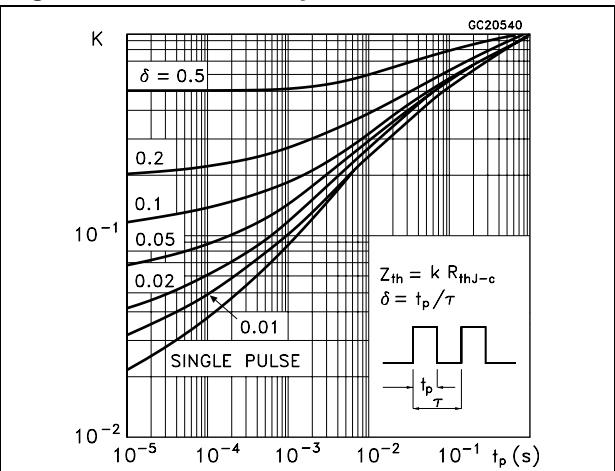


Figure 4. Safe operating area for TO-220FP

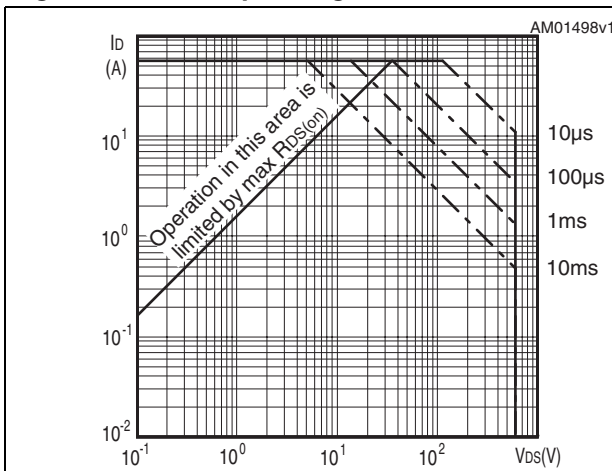


Figure 5. Thermal impedance for TO-220FP

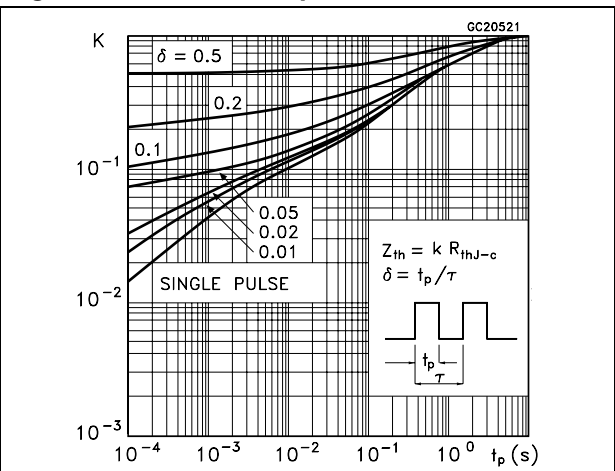


Figure 6. Safe operating area for TO-247

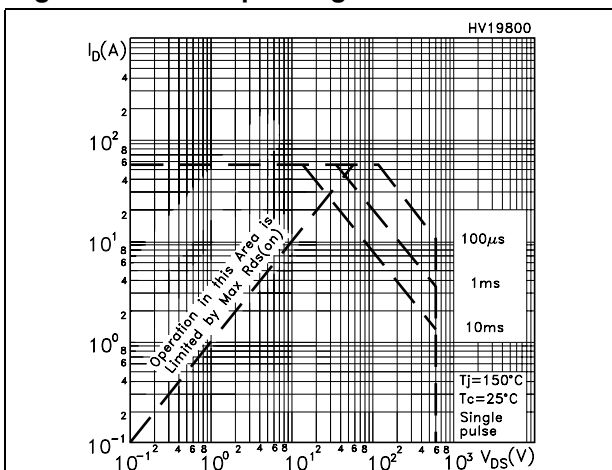


Figure 7. Thermal impedance for TO-247

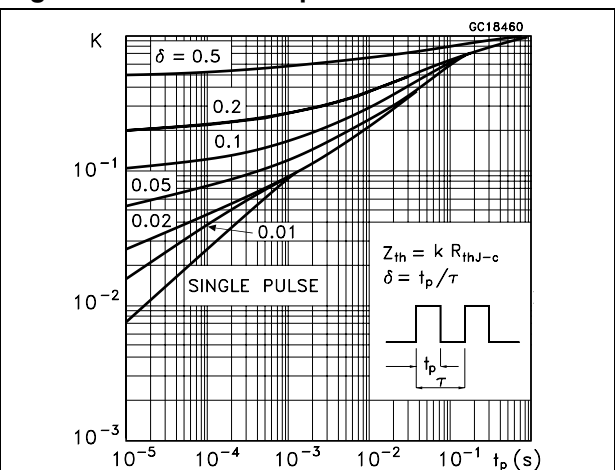


Figure 8. Output characteristics

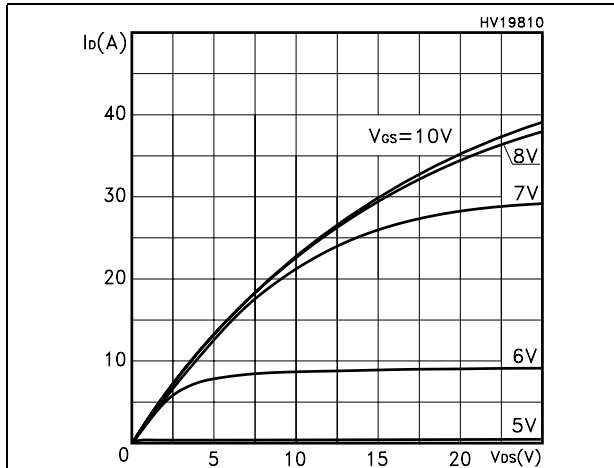


Figure 9. Transfer characteristics

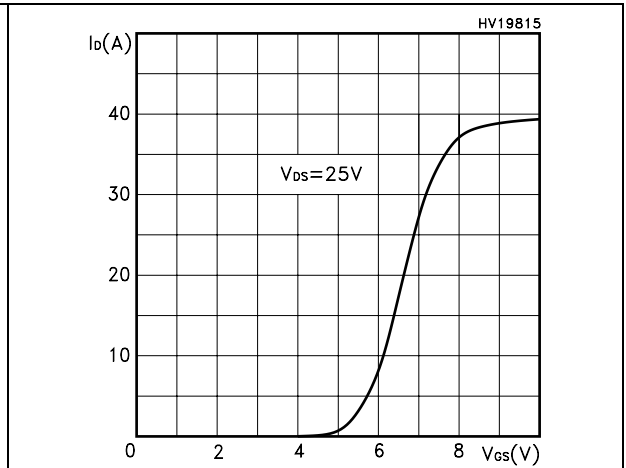


Figure 10. Normalized  $BV_{DSS}$  vs temperature

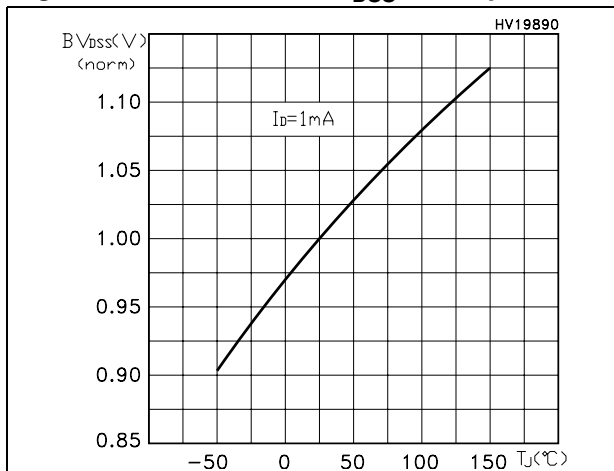


Figure 11. Static drain-source on resistance

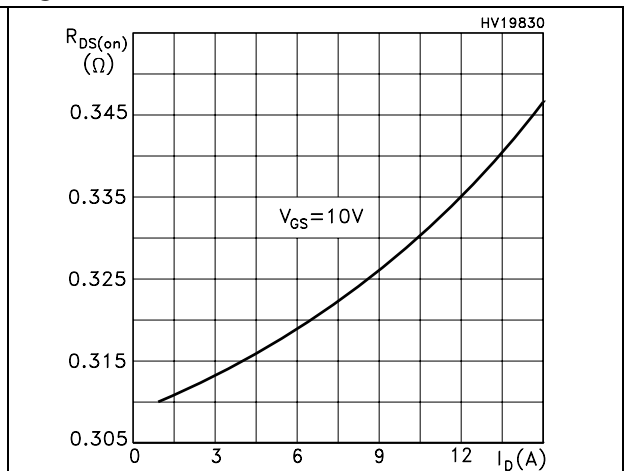


Figure 12. Gate charge vs gate-source voltage

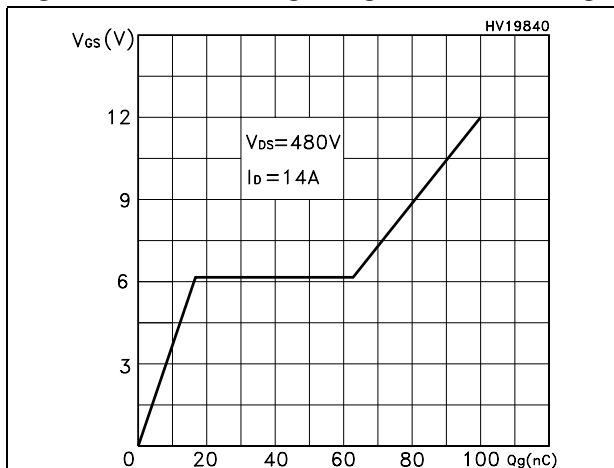


Figure 13. Capacitance variations

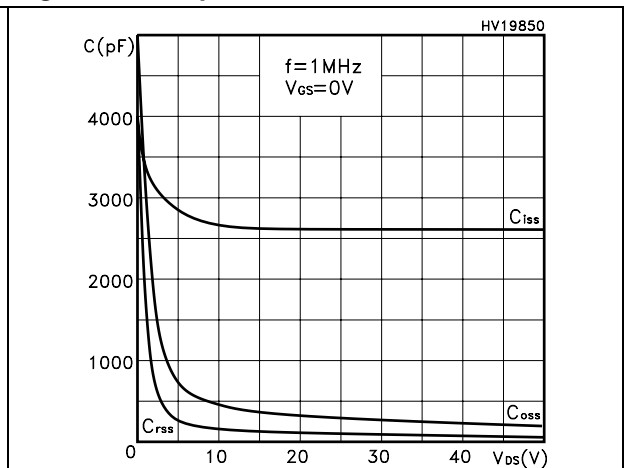


Figure 14. Normalized gate threshold voltage vs temperature

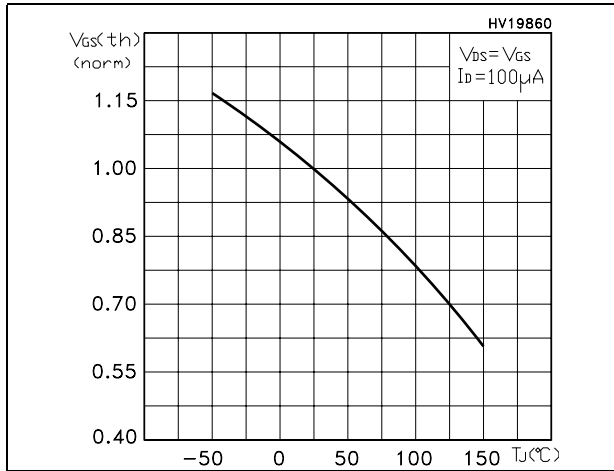


Figure 15. Normalized on resistance vs temperature

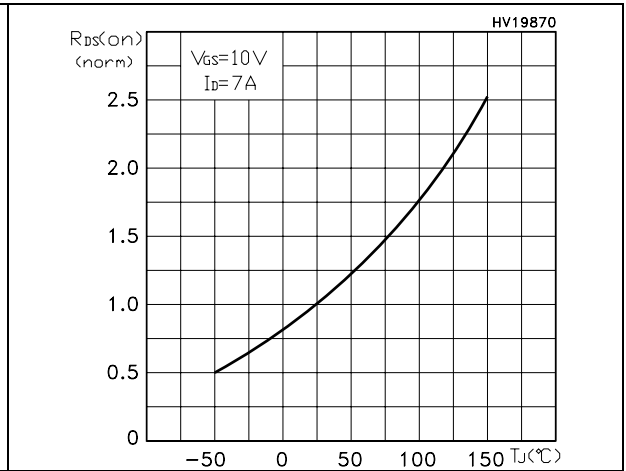


Figure 16. Source-drain diode forward characteristics

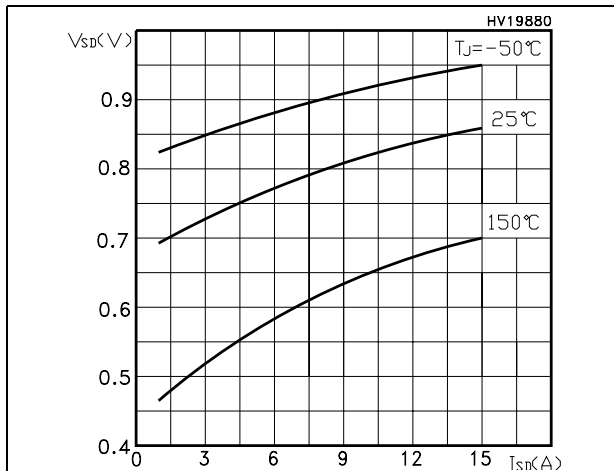
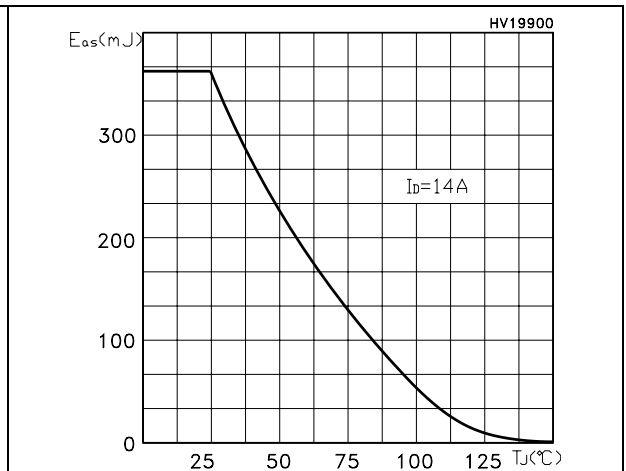


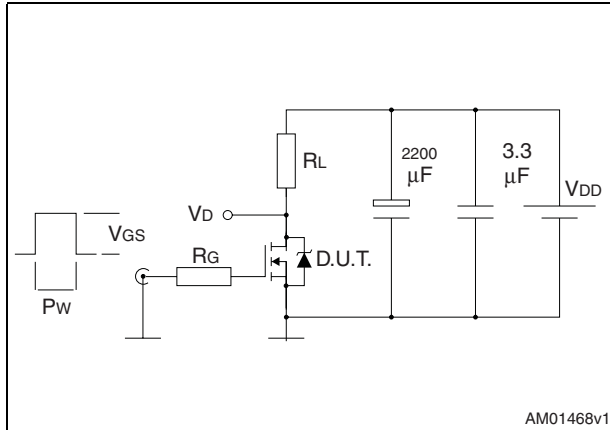
Figure 17. Maximum avalanche energy vs temperature



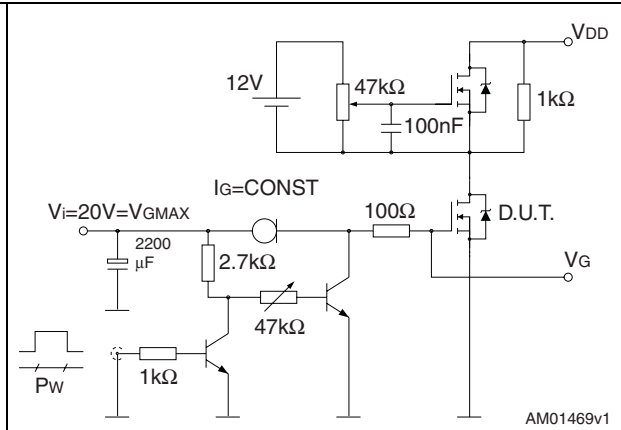


### 3 Test circuits

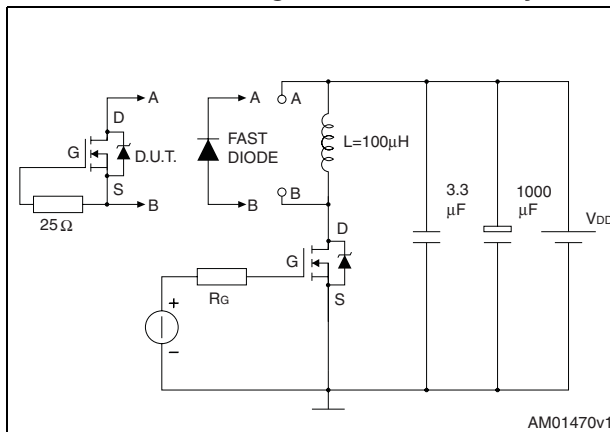
**Figure 18. Switching times test circuit for resistive load**



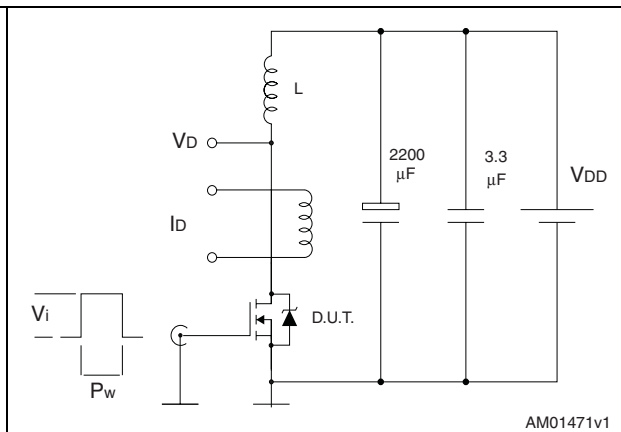
**Figure 19. Gate charge test circuit**



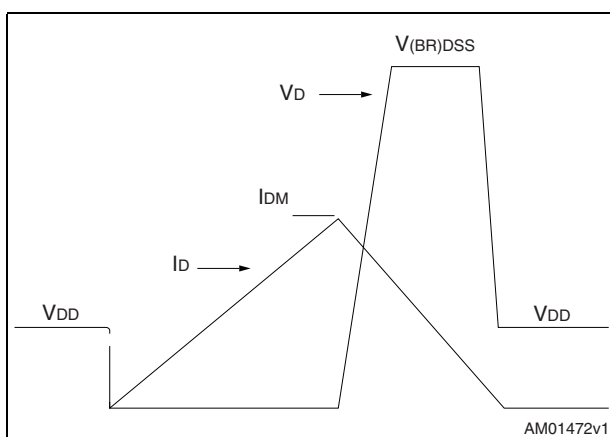
**Figure 20. Test circuit for inductive load switching and diode recovery times**



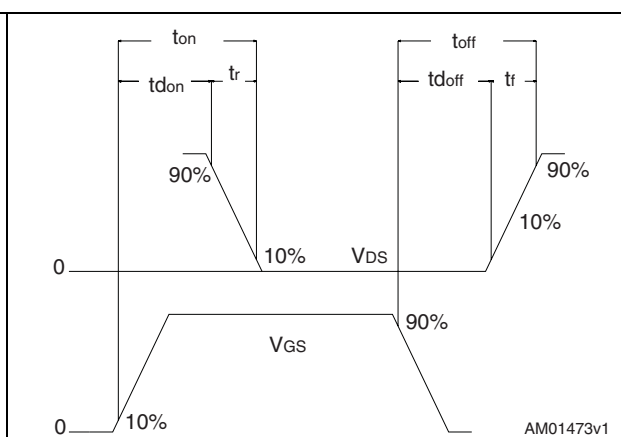
**Figure 21. Unclamped inductive load test circuit**



**Figure 22. Unclamped inductive waveform**



**Figure 23. Switching time waveform**



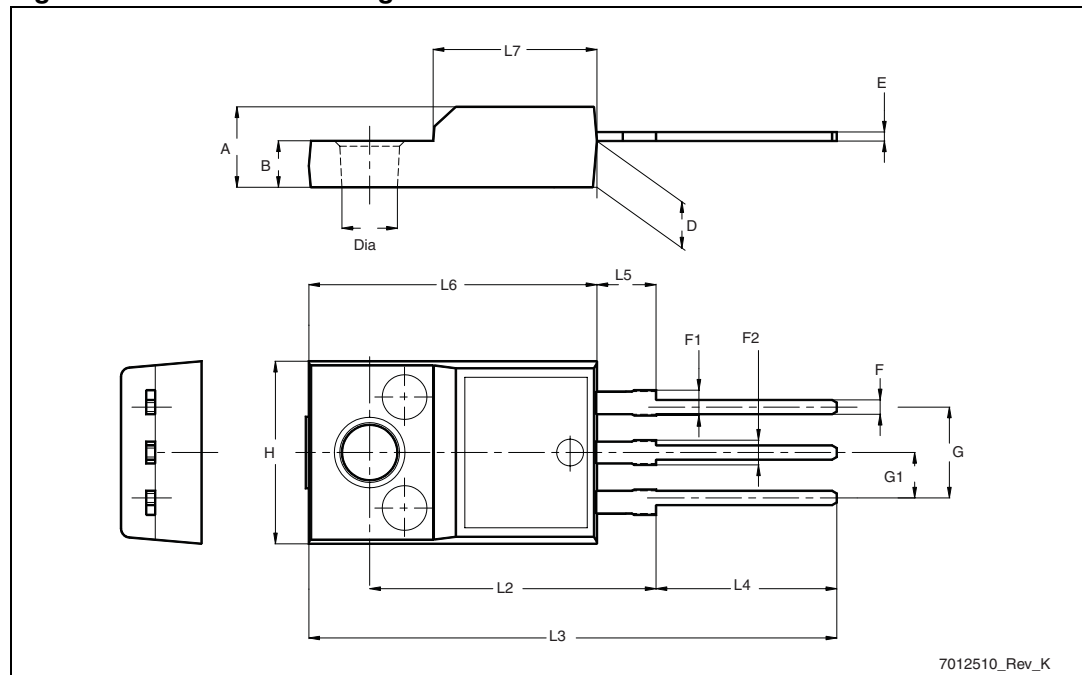
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 10. TO-220FP mechanical data

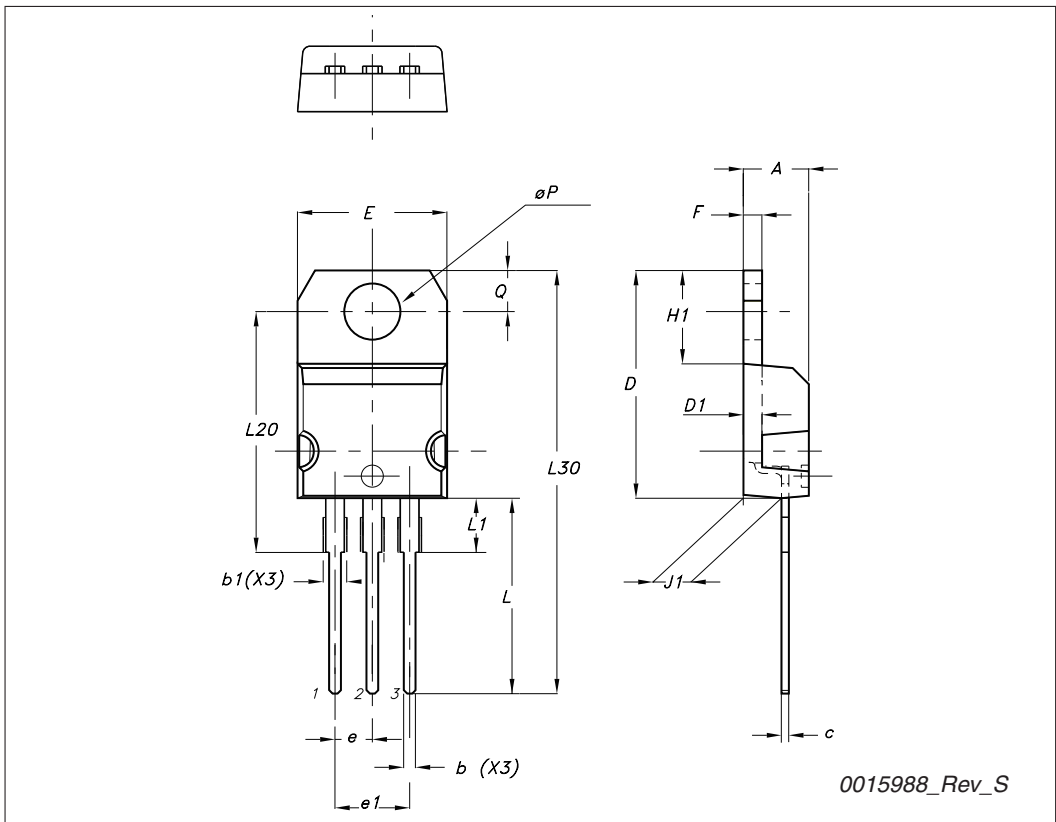
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 24. TO-220FP drawing



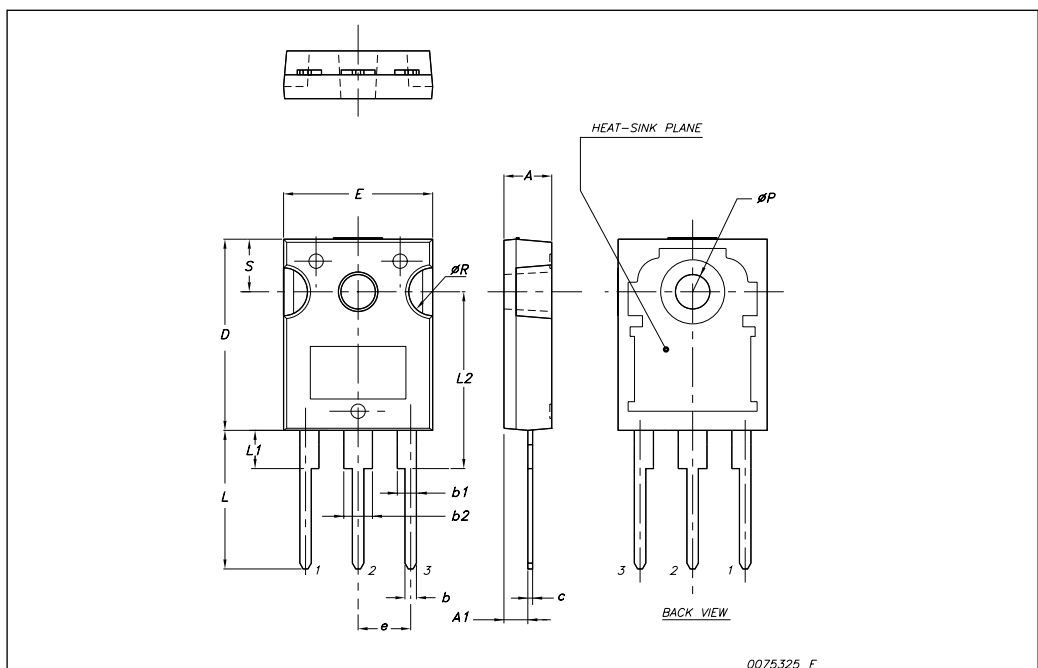
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



## TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
$\phi P$	3.55		3.65
$\phi R$	4.50		5.50
S		5.50	



## 5 Revision history

**Table 11. Document revision history**

Date	Revision	Changes
11-Sep-2006	3	
07-Jun-2007	4	Added statement for ECOPACK®.
04-Dec-2009	5	Updated packages mechanical data.

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